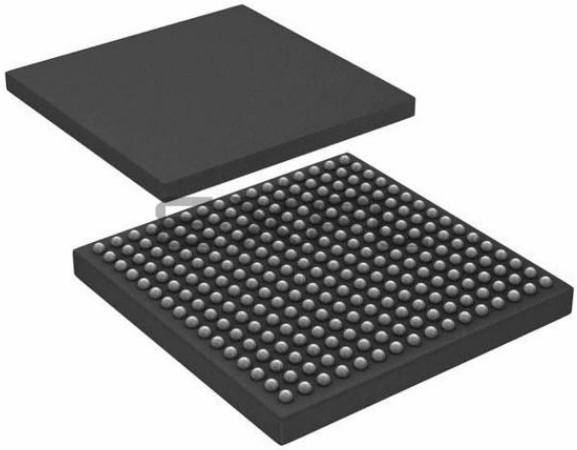

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	9216
Total RAM Bits	55296
Number of I/O	178
Number of Gates	400000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl400v2-fg256i

Temperature Grade Offerings

Package	AGL015 [1]	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000
					M1AGL250		M1AGL600	M1AGL1000
QN48	–	C, I	–	–	–	–	–	–
QN68	C, I	–	–	–	–	–	–	–
UC81	–	C, I	–	–	–	–	–	–
CS81	–	C, I	–	–	–	–	–	–
CS121	–	–	C, I	C, I	–	–	–	–
VQ100	–	C, I	C, I	C, I	C, I	–	–	–
QN132[2]	–	C, I	C, I [2]	C, I	–	–	–	–
CS196	–	–	–	C, I	C, I	C, I	–	–
FG144	–	–	–	C, I	C, I	C, I	C, I	C, I
FG256	–	–	–	–	–	C, I	C, I	C, I
CS281	–	–	–	–	–	–	C, I	C, I
FG484	–	–	–	–	–	C, I	C, I	C, I

Notes:
1. *AGL015 is not recommended for new designs.*
2. *Package not available.*

C = Commercial temperature range: 0°C to 85°C junction temperature.
I = Industrial temperature range: –40°C to 100°C junction temperature.

IGLOO Device Status

IGLOO Devices	Status	M1 IGLOO Devices	Status
AGL015	Not recommended for new designs.		
AGL030	Production		
AGL060	Production		
AGL125	Production		
AGL250	Production	M1AGL250	Production
AGL400	Production		
AGL600	Production	M1AGL600	Production
AGL1000	Production	M1AGL1000	Production

References made to IGLOO devices also apply to ARM-enabled IGLOOe devices. The ARM-enabled part numbers start with M1 (Cortex-M1).

Contact your local Microsemi SoC Products Group representative for device availability: www.microsemi.com/soc/contact/default.aspx.

AGL015 and AGL030

The AGL015 and AGL030 are architecturally compatible; there are no RAM or PLL features.

Devices Not Recommended For New Designs

AGL015 is not recommended for new designs.

Power Consumption of Various Internal Resources

Table 2-19 • **Different Components Contributing to Dynamic Power Consumption in IGLOO Devices For IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Dynamic Power (µW/MHz)							
		AGL1000	**AGL600**	**AGL400**	**AGL250**	**AGL125**	**AGL060**	**AGL030**	**AGL015**
PAC1	Clock contribution of a Global Rib	7.778	6.221	6.082	4.460	4.446	2.736	0.000	0.000
PAC2	Clock contribution of a Global Spine	4.334	3.512	2.759	2.718	1.753	1.971	3.483	3.483
PAC3	Clock contribution of a VersaTile row	1.379	1.445	1.377	1.483	1.467	1.503	1.472	1.472
PAC4	Clock contribution of a VersaTile used as a sequential module	0.151	0.149	0.151	0.149	0.149	0.151	0.146	0.146
PAC5	First contribution of a VersaTile used as a sequential module	0.057							
PAC6	Second contribution of a VersaTile used as a sequential module	0.207							
PAC7	Contribution of a VersaTile used as a combinatorial module	0.276	0.262	0.279	0.277	0.280	0.300	0.281	0.273
PAC8	Average contribution of a routing net	1.161	1.147	1.193	1.273	1.076	1.088	1.134	1.153
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic PLL contribution	2.70							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Table 2-22 • **Different Components Contributing to the Static Power Consumption in IGLOO Device For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Static Power (mW)							
		AGL1000	**AGL600**	**AGL400**	**AGL250**	**AGL125**	**AGL060**	**AGL030**	**AGL015**
PDC1	Array static power in Active mode	See Table 2-12 on page 2-9.							
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-8.							
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7.							
PDC4	Static PLL contribution	0.90							
PDC5	Bank quiescent power (VCCI-Dependent)	See Table 2-12 on page 2-9.							
PDC6	I/O input pin static power (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PDC7	I/O output pin static power (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Table 2-26 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings**
Applicable to Standard Plus I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range[3]	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVCMOS	8 mA	8 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	8	8
1.5 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4
1.2 V LVCMOS[4]	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range[4]	100 µA	2 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	1.575	0.1	VCCI – 0.1	0.1	0.1
3.3 V PCI	Per PCI specifications										
3.3 V PCI-X	Per PCI-X specifications										

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-40 • I/O Output Buffer Maximum Resistances[1]
Applicable to Standard I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
1.5 V LVCMOS	2 mA	200	224
1.2 V LVCMOS	1 mA	158	164
1.2 V LVCMOS Wide Range[4]	100 µA	Same as regular 1.2 V LVCMOS	Same as regular 1.2 V LVCMOS

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (VOLspec) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (VCCImax - VOHspec) / I_{OHspec}$

Table 2-41 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

	$R_{(WEAK\ PULL\text{-}UP)}$[1] ($\Omega$)		$R_{(WEAK\ PULL\text{-}DOWN)}$[2] ($\Omega$)	
VCCI	**Min.**	**Max.**	**Min.**	**Max.**
3.3 V	10 K	45 K	10 K	45 K
3.3 V Wide Range I/Os	10 K	45 K	10 K	45 K
2.5 V	11 K	55 K	12 K	74 K
1.8 V	18 K	70 K	17 K	110 K
1.5 V	19 K	90 K	19 K	140 K
1.2 V	25 K	110 K	25 K	150 K
1.2 V Wide Range I/Os	19 K	110 K	19 K	150 K

Notes:

1. $R_{(WEAK\ PULL\text{-}UP\text{-}MAX)} = (VCCImax - VOHspec) / I_{(WEAK\ PULL\text{-}UP\text{-}MIN)}$
2. $R_{(WEAK\ PULLDOWN\text{-}MAX)} = (VOLspec) / I_{(WEAK\ PULLDOWN\text{-}MIN)}$

Table 2-49 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks**

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		V_{OL}	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

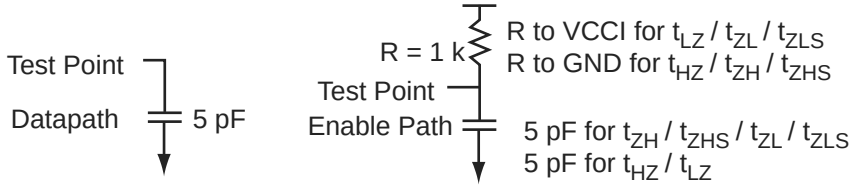


Figure 2-7 • **AC Loading**

Table 2-50 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

*Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Table 2-97 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	9	11	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	17	22	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

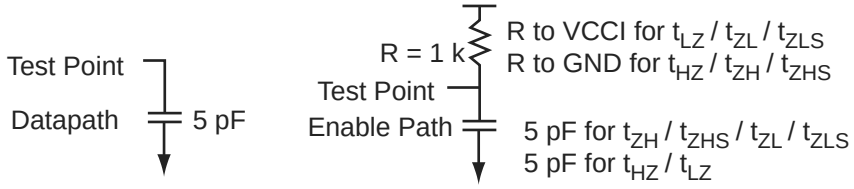


Figure 2-9 • AC Loading

Table 2-98 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.8	0.9	5

*Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-99 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	6.38	0.18	1.01	0.66	6.51	5.93	2.33	1.56	10.10	9.53	ns
4 mA	Std.	0.97	5.35	0.18	1.01	0.66	5.46	5.04	2.67	2.38	9.05	8.64	ns
6 mA	Std.	0.97	4.62	0.18	1.01	0.66	4.71	4.44	2.90	2.79	8.31	8.04	ns
8 mA	Std.	0.97	4.37	0.18	1.01	0.66	4.46	4.31	2.95	2.89	8.05	7.90	ns
12 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns
16 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-104 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	2.62	0.18	0.98	0.66	2.67	2.59	1.67	1.29	2.62	ns
4 mA	Std.	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	2.18	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.2 V DC Core Voltage

Table 2-105 • 1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.97	0.26	1.11	1.10	7.08	6.48	2.87	2.29	12.87	12.27	ns
4 mA	Std.	1.55	5.91	0.26	1.11	1.10	6.01	5.57	3.21	3.14	11.79	11.36	ns
6 mA	Std.	1.55	5.16	0.26	1.11	1.10	5.24	4.95	3.45	3.55	11.03	10.74	ns
8 mA	Std.	1.55	4.90	0.26	1.11	1.10	4.98	4.81	3.50	3.66	10.77	10.60	ns
12 mA	Std.	1.55	4.83	0.26	1.11	1.10	4.90	4.83	3.58	4.08	10.68	10.61	ns
16 mA	Std.	1.55	4.83	0.26	1.11	1.10	4.90	4.83	3.58	4.08	10.68	10.61	ns

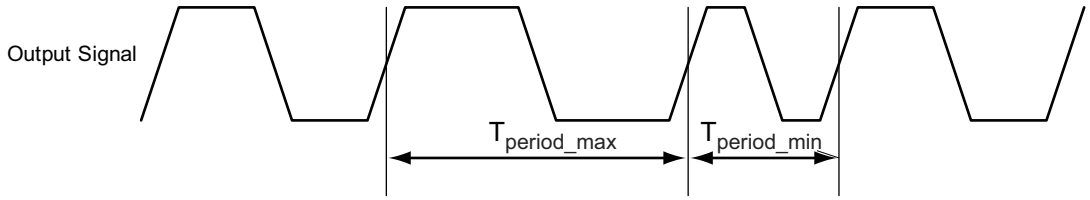
Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-106 • 1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.73	0.26	1.11	1.10	3.71	3.73	2.86	2.34	9.49	9.51	ns
4 mA	Std.	1.55	3.12	0.26	1.11	1.10	3.16	2.97	3.21	3.22	8.95	8.75	ns
6 mA	Std.	1.55	2.79	0.26	1.11	1.10	2.83	2.59	3.45	3.65	8.62	8.38	ns
8 mA	Std.	1.55	2.73	0.26	1.11	1.10	2.77	2.52	3.50	3.75	8.56	8.30	ns
12 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns
16 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*



Note: Peak-to-peak jitter measurements are defined by $T_{peak\text{-}to\text{-}peak} = T_{period\_max} – T_{period\_min}$.

Figure 2-30 • **Peak-to-Peak Jitter Definition**

VJTAG JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND. It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

VPUMP Programming Supply Voltage

IGLOO devices support single-voltage ISP of the configuration flash and FlashROM. For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in the datasheet.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01 µF and 0.33 µF capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

User Pins

I/O User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

GL Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *IGLOO FPGA Fabric User Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the "I/O Structures in IGLOO and ProASIC3 Devices" chapter of the *IGLOO FPGA Fabric User Guide* for an explanation of the naming of global pins.

FF Flash*Freeze Mode Activation Pin

Flash*Freeze mode is available on IGLOO devices. The FF pin is a dedicated input pin used to enter and exit Flash*Freeze mode. The FF pin is active low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash*Freeze mode is not used in the design, the FF pin is available as a regular I/O.

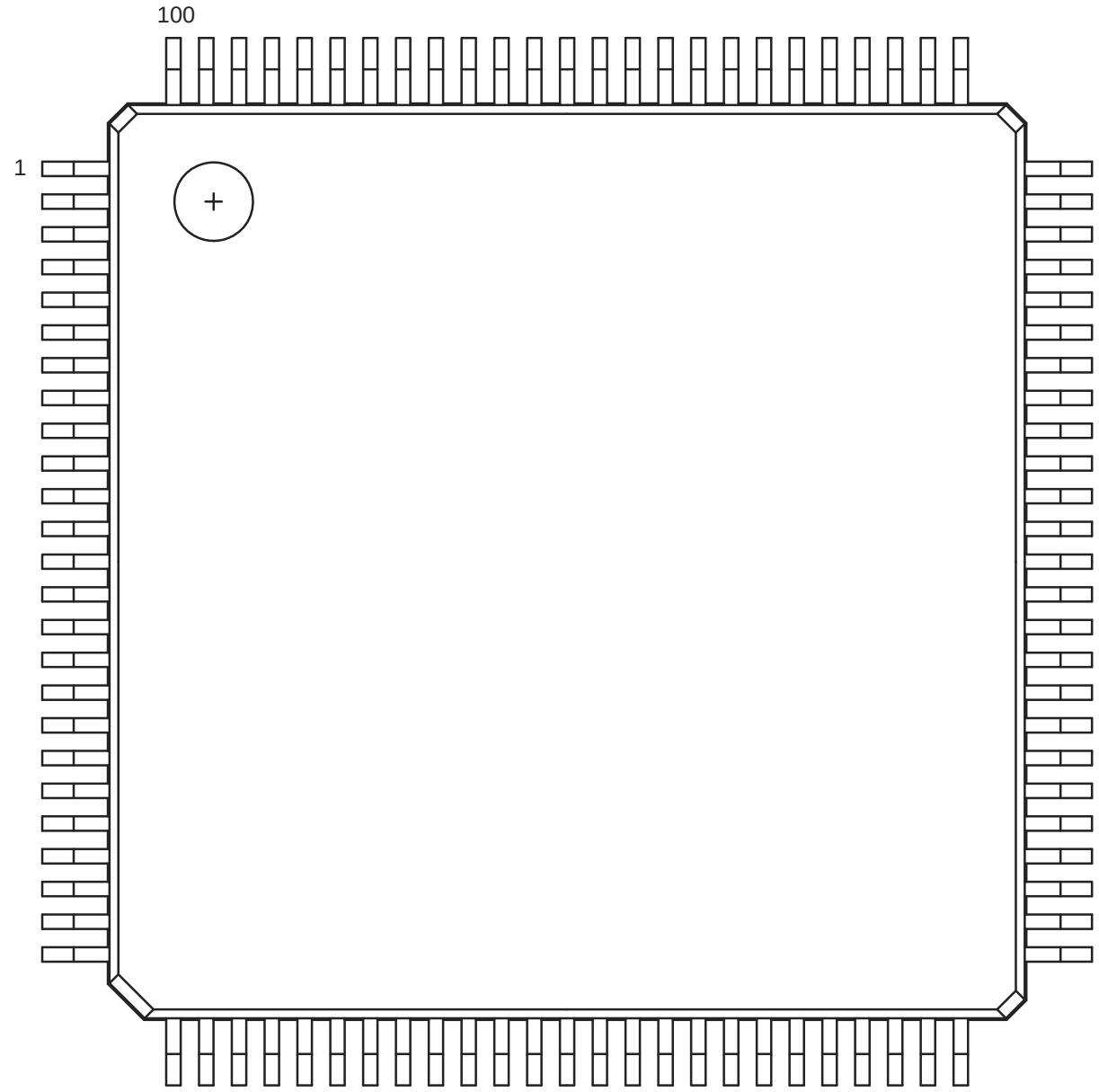
When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

CS81	
Pin Number	**AGL030 Function**
A1	IO00RSB0
A2	IO02RSB0
A3	IO06RSB0
A4	IO11RSB0
A5	IO16RSB0
A6	IO19RSB0
A7	IO22RSB0
A8	IO24RSB0
A9	IO26RSB0
B1	IO81RSB1
B2	IO04RSB0
B3	IO10RSB0
B4	IO13RSB0
B5	IO15RSB0
B6	IO20RSB0
B7	IO21RSB0
B8	IO28RSB0
B9	IO25RSB0
C1	IO79RSB1
C2	IO80RSB1
C3	IO08RSB0
C4	IO12RSB0
C5	IO17RSB0
C6	IO14RSB0
C7	IO18RSB0
C8	IO29RSB0
C9	IO27RSB0
D1	IO74RSB1
D2	IO76RSB1
D3	IO77RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	IO23RSB0
D8	IO31RSB0
D9	IO30RSB0

CS81	
Pin Number	**AGL030 Function**
E1	GEB0/IO71RSB1
E2	GEA0/IO72RSB1
E3	GEC0/IO73RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GDC0/IO32RSB0
E8	GDA0/IO33RSB0
E9	GDB0/IO34RSB0
F1	IO68RSB1
F2	IO67RSB1
F3	IO64RSB1
F4	GND
F5	VCCIB1
F6	IO47RSB1
F7	IO36RSB0
F8	IO38RSB0
F9	IO40RSB0
G1	IO65RSB1
G2	IO66RSB1
G3	IO57RSB1
G4	IO53RSB1
G5	IO49RSB1
G6	IO44RSB1
G7	IO46RSB1
G8	VJTAG
G9	TRST
H1	IO62RSB1
H2	FF/IO60RSB1
H3	IO58RSB1
H4	IO54RSB1
H5	IO48RSB1
H6	IO43RSB1
H7	IO42RSB1
H8	TDI
H9	TDO

CS81	
Pin Number	**AGL030 Function**
J1	IO63RSB1
J2	IO61RSB1
J3	IO59RSB1
J4	IO56RSB1
J5	IO52RSB1
J6	IO45RSB1
J7	TCK
J8	TMS
J9	VPUMP

VQ100



Note: This is the top view of the package.

Note

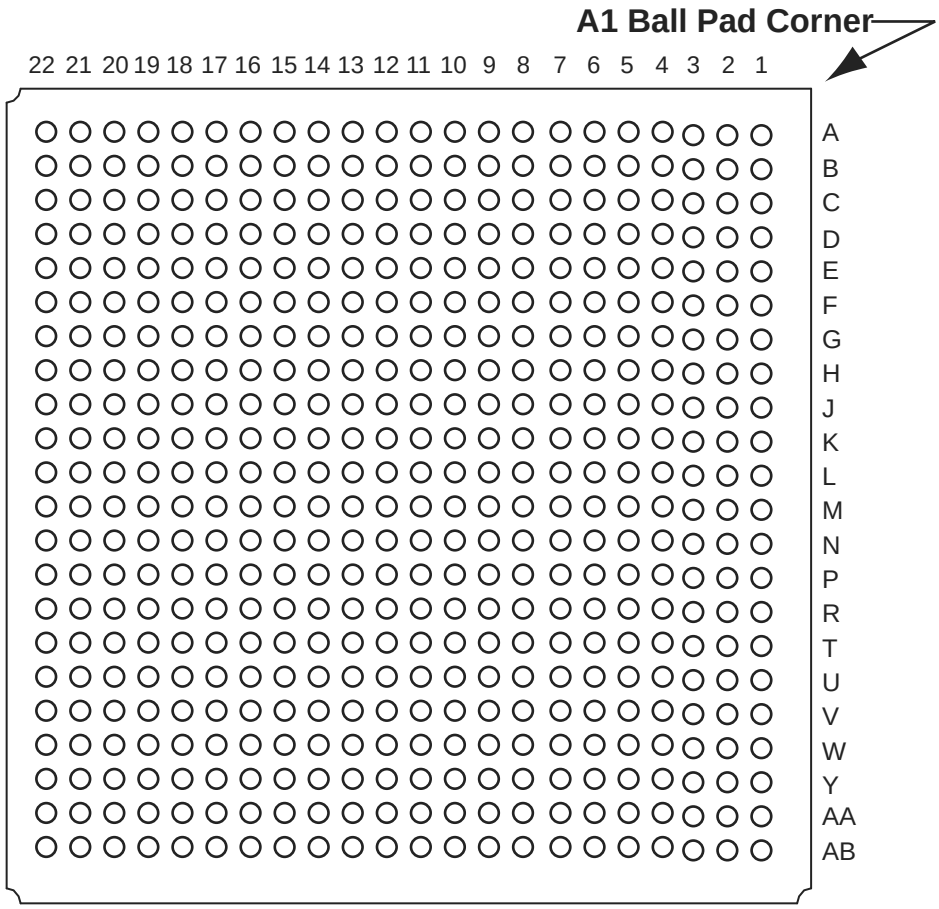
For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

VQ100	
Pin Number	**AGL125 Function**
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	FF/GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1

VQ100	
Pin Number	**AGL125 Function**
36	IO93RSB1
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0

VQ100	
Pin Number	**AGL125 Function**
72	IO42RSB0
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

FG484



Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG484	
Pin Number	**AGL400 Function**
E13	IO38RSB0
E14	IO42RSB0
E15	GBC1/IO55RSB0
E16	GBB0/IO56RSB0
E17	IO44RSB0
E18	GBA2/IO60PDB1
E19	IO60NDB1
E20	GND
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO154VDB3
F5	IO155VDB3
F6	IO11RSB0
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO45RSB0
F15	GBC0/IO54RSB0
F16	IO48RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	NC
G2	NC
G3	NC
G4	IO151VDB3

FG484	
Pin Number	**AGL400 Function**
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO67PPB1
K17	IO64NPB1
K18	IO73PDB1
K19	IO73NDB1
K20	NC
K21	NC
K22	NC
L1	NC
L2	NC
L3	NC
L4	GFB0/IO146NPB3
L5	GFA0/IO145NDB3
L6	GFB1/IO146PPB3
L7	VCOMPLF
L8	GFC0/IO147NPB3
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO67NPB1
L16	GCB1/IO68PPB1
L17	GCA0/IO69NPB1
L18	NC
L19	GCB0/IO68NPB1
L20	NC
L21	NC
L22	NC
M1	NC
M2	NC

FG484	
Pin Number	**AGL400 Function**
R9	VCCIB2
R10	VCCIB2
R11	IO108RSB2
R12	IO101RSB2
R13	VCCIB2
R14	VCCIB2
R15	VMV2
R16	IO83RSB2
R17	GDB1/IO78UPB1
R18	GDC1/IO77UDB1
R19	IO75NDB1
R20	VCC
R21	NC
R22	NC
T1	NC
T2	NC
T3	NC
T4	IO140NDB3
T5	IO138PPB3
T6	GEC1/IO137PPB3
T7	IO131RSB2
T8	GNDQ
T9	GEA2/IO134RSB2
T10	IO117RSB2
T11	IO111RSB2
T12	IO99RSB2
T13	IO94RSB2
T14	IO87RSB2
T15	GNDQ
T16	IO93RSB2
T17	VJTAG
T18	GDC0/IO77VDB1
T19	GDA1/IO79UDB1
T20	NC
T21	NC
T22	NC

FG484	
Pin Number	**AGL600 Function**
C21	NC
C22	VCCIB1
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0
D7	GAB0/IO02RSB0
D8	IO11RSB0
D9	IO16RSB0
D10	IO18RSB0
D11	IO28RSB0
D12	IO34RSB0
D13	IO37RSB0
D14	IO41RSB0
D15	IO43RSB0
D16	GBB1/IO57RSB0
D17	GBA0/IO58RSB0
D18	GBA1/IO59RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO173PDB3
E5	GAA2/IO174PDB3
E6	GNDQ
E7	GAB1/IO03RSB0
E8	IO13RSB0
E9	IO14RSB0
E10	IO21RSB0
E11	IO27RSB0
E12	IO32RSB0

FG484	
Pin Number	**AGL1000 Function**
G5	IO222PDB3
G6	GAC2/IO223PDB3
G7	IO223NDB3
G8	GNDQ
G9	IO23RSB0
G10	IO29RSB0
G11	IO33RSB0
G12	IO46RSB0
G13	IO52RSB0
G14	IO60RSB0
G15	GNDQ
G16	IO80NDB1
G17	GBB2/IO79PDB1
G18	IO79NDB1
G19	IO82NPB1
G20	IO85PDB1
G21	IO85NDB1
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO217PDB3
H5	IO218PDB3
H6	IO221NDB3
H7	IO221PDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO38RSB0
H12	IO47RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO80PDB1
H17	IO83PPB1
H18	IO86PPB1

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